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David F. Barber, Sr.

1923 – 1999

Co-Chairman of IRPS - 1964

General Chairman of IRPS - 1973

IRPS Board of Directors - For Many Years

This Proceedings of the International Reliability Physics Symposium is dedicated to David F. Barber, Sr. one of the founding fathers of the Symposium and life long member of the IRPS family.

Mr. Barber served in many roles in support of the symposium. He was Branch Chief of the group at Rome Air Development Center that came up with the idea for the First Annual Symposium on the Physics of Failure in Electronics in 1962. Then he managed the organization that was the financial sponsor of the Symposium as it grew in size and reputation. Mr. Barber was Co-Chair of the Symposium in 1964 and Chairman in 1973. During the years from 1979 and into the 1980's he took over the job of gathering the papers, proof reading and seeing to it that the Proceedings came out on time each year. Also it was during the 1980's after he had retired from RADC in 1979 that he formed Scien-Tech Associates

and was contracted by the IRPS BOD to perform the negotiations with the hotel properties for site selection. Scien-Tech also assisted in the arrangements for the Symposium and has been one of the key factors in having a smoothly run Symposium each year.

Mr. Barber received the IRPS Award for Outstanding Contributions in the Field of Reliability Physics in 1984 recognizing his leadership in establishing the discipline that many of us have chosen for our careers.

It is fitting to dedicate the IRPS Proceedings for year 2000 to Mr. Barber as the Symposium begins a new century of activity. To those of us that have been associated with the Symposium for these many years, Mr. Barber will always be an inspiration and a member of the IRPS family.